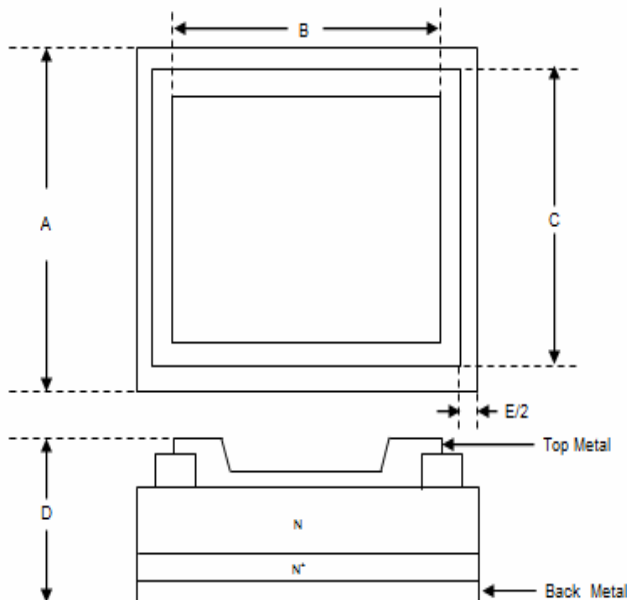


### Planar MOS-Controlled Diode Wafer (PMCD)



Item	Dimensions	
	um	mil
Die Size (A)	2540	100
Top Metal Pad Size (B)	2440	96
Passivation Seal (C)	2460	96.8
Wafer Thickness (D)	240	9.4
Scribe Line Width (E)	80	3.14
Other Informations		
Wafer Size	6"	
Gross Die	2420	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C				
Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.3mA	$V_{RRM}$	45	51	V
Maximum Average Forward Rectified Current	$I_O$	15	-	A
Forward Voltage Drop, @ $I_F=2A$ @ $I_F=5A$ @ $I_F=10A$ @ $I_F=15A$	$V_F$	- 0.41 0.45 0.52	0.35 - - -	V
Maximum Reverse Current at Rated $V_{RRM}$	$I_R$	130	110	$\mu A$
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$	250	-	A
Operating Temperature Range	$T_J$	-50 to +150	-	°C
Storage Temperature Range	$T_{STG}$	-50 to +150	-	°C
ESD(IEC61000-4-2)	Contact	20	-	KV